



74AHCT595

8-BIT SHIFT REGISTER 8-BIT OUTPUT REGISTER

Description

The 74AHCT595 is an advanced high speed CMOS device that is designed to be pin compatable with 74LS low power Schottky types.

An eight bit shift register accepts data from the serial input (DS) on each positive transition of the shift register clock (STCP). When asserted low, the reset function ($\overline{\text{MR}}$) sets all shift register values to zero and is independent of all clocks.

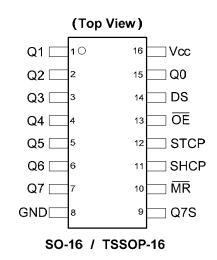
Data from the input serial shift register is placed in the output register with a rising pulse on the storages resister clock (SHCP). With the output enable $(\overline{\text{OE}})$ asserted low the 3-state outputs Q0-Q7 become active and present.

All registers capture data on rising edge and change output on the falling edge. If both clocks are connected together, the input shift register is always one clock cycle ahead of the output register.

Features

- Supply Voltage Range from 4.5V to 5.5V
- Sinks or sources 8mA at V_{CC} = 4.5V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 - Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 250mA per JESD 78, Class II
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



Applications

- General Purpose Logic
- Serial to Parallel Data conversion
- Capture and hold data for extended periods of time.
- Allow simple serial bit streams from a microcontroller to control as many peripheral lines as needed.
- Wide array of products such as:
 - Computer peripherals
 - Appliances
 - Industrial control
- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

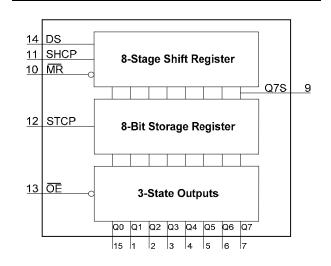
Click here for ordering information, located at the end of datasheet



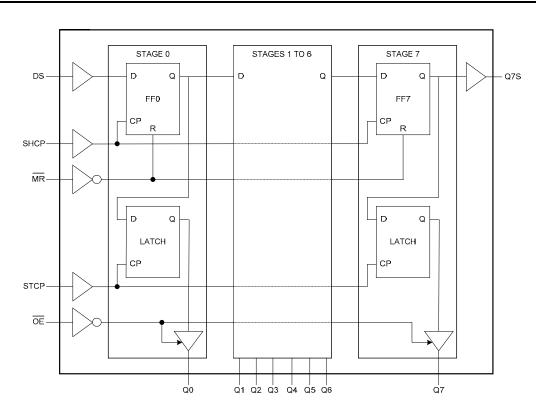
Pin Descriptions

	-	
Pin Number	Pin Name	Description
1	Q1	Parallel Data Output 1
2	Q2	Parallel Data Output 2
3	Q3	Parallel Data Output 3
4	Q4	Parallel Data Output 4
5	Q5	Parallel Data Output 5
6	Q6	Parallel Data Output 6
7	Q7	Parallel Data Output 7
8	GND	Ground
9	Q7S	Serial Data Output
10	MR	Master Reset Input
11	SHCP	Shift Register Clock Input
12	STCP	Storage Register Clock Input
13	OE	Output Enable Input
14	DS	Serial Data Input
15	Q0	Parallel Data Output 0
16	Vcc	Supply Voltage

Functional Diagram



Logic Diagram





Functional Description and Timing Diagram

	Con	trol		Input	0	utput	Function
SHCP	STCP	OE	MR	DS	Q7S	Qn	Function
х	х	L	L	-	NC		Low-level asserted on MR clears shift register. Storage register is unchanged
Х	1	L	L	-	L L		Empty shift register transferred to storage register
Х	Х	Н	L	-	L Z		Shift register remains clear;: All Q ouputs in Z state.
Ť	x	L	н	_	Q6S	NC	HIGH is shifted into first stage of Shift Register Contents of each register shifted to next register The content of Q6S has been shifted to Q7S and now appears on device pin Q7S
х	1	L	н	_	NC	QnS	Contents of shift register copied to storage register. With output now in active state the storage resister contents appear on Q outputs.
↑	1	L	Н	-	Q6S QnS		Contents of shift register copied to output register then shift register shifted.

H=HIGH voltage state L=LOW voltage state ^=LOW to HIGH transition X= don't care – high or low (not floating)

NC= No change

Z= high-impedance state

SHCP	
DS	
STCP	
MR	
ŌĒ	
Q0	
Q 1	
Q6	
Q7	Z-state
Q7S	



Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
l _{IK}	Input Clamp Current VI < -0.5V	-20	mA
I _{OK}	Output Clamp Current V _O <-0.5V	-20	mA
I _{OK}	Output Clamp Current $V_O > V_{CC} + 0.5V$	20	mA
lo	Continuous output current	±25	mA
Icc	Continuous current through Vcc or GND	75	mA
I _{GND} Continuous current through Vcc or GND		-75	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
Ртот	Total Power Dissipation	500	mW

Absolute Maximum Ratings (Note 4) (@T_A = +25°C, unless otherwise specified.)

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	Supply Voltage	_	4.5	5.5	V
VI	Input Voltage	-	0	5.5	V
Vo	Output Voltage	Active Mode	0	V _{CC}	V
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 4.5V to 5.5V	-	20	ns/V
T _A	Operating free-air temperature	-	-40	+125	°C

Note: 5. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Symbol	Baramatar	Test Conditions	N	TA	= +25°	С	T _A = -40°	C to +85°C	T _A = -40°	C to +125°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	High-Level Input Voltage	_	4.5V to 5.5V	2.0	-	-	2.0	-	2.0	_	V
VIL	Low-Level Input voltage	_	4.5V to 5.5V	-	-	0.8	-	0.8	-	0.8	V
V	High-Level	I _{OH} = -50μA	4.5V	4.4	4.5	-	4.4	-	4.4	-	v
V _{OH}	Output Voltage	I _{OH} = -8mA	4.5V	3.94	-	-	3.80	-	3.70	-	V
	Low-Level I _{OL} = 50µA	4.51/	-	0	0.1	-	0.1	-	0.1	v	
V _{OL}	Output Voltage	I _{OL} = 8mA	4.5V	_	-	0.36	-	0.44	_	0.55	v
h	Input Current	V _I =GND to 5.5V	0 to 5.5V	_	0.1	± 1	_	± 1	-	± 2	μA
I _{OZ}	Z-state Leakage Current	$V_0 = Vcc \text{ or GND}$ $\overline{OE} = HIGH$	5.5V	_	_	± 0.25	_	2.5	-	10	μA
I _{CC}	Supply Current	$V_I = GND \text{ or } V_{CC}$ $I_O = 0$	5.5V	_	_	4.0	-	40	-	80	μA
ΔI_{CC}	Additional Supply Current per Input	$V_{I} = Vcc - 2.1V$ $I_{O} = 0$	4.5V to 5.5V	_	-	1.35	-	1.5	_	1.5	mA
Ci	Input Capacitance	$V_i = V_{CC}$ or GND	5.5V	_	4	10	_	10	_	10	pF



Switching Characteristics

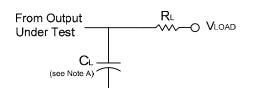
Symbol /	Dive	To al O an dition of		Т	A = +25°	C	-40°C te	o +85°C	-40°C to	+125°C	11
Parameter	Pins	Test Conditions	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
f _{MAX} Maximum Frequency	SHCP or STCP	Figure 1	4.5V to 5.5V	130	170	-	110	_	90	_	MHz
	SHCP HIGH or LOW	Figure 1	4.5V to 5.5V	5.0	-	-	5.0	-	5.0	-	
t _W Pulse Width	STCP HIGH or LOW	Figure 1	4.5V to 5.5V	5.0	_	-	5.0	-	5.0	-	ns
	MR LOW	Figure 1	4.5V to 5.5V	5.0	-	-	5.0	-	5.0	-	
ts∪	DS to SHCP	Figure 1	4.5V to 5.5V	3.0	-	-	3.0	-	3.0	-	ns
Set-up Time	SHCP to STCP	Figure 1	4.5V to 5.5V	5.0	-	-	5.0	_	5.0	-	ns
t _H Hold Time	DS to SHCP	Figure 1	4.5V to 5.5V	2.0	-	-	2.0	-	2.0	-	ns
t _{REC} Recovery Time	MR to SHCP	Figure 1	4.5V to 5.5V	3.0	-	-	3.0	-	3.0	_	ns
	SHCP to Q7S	Figure 1 C _L = 15pF	4.5V to 5.5V	_	3.8	8.2	1.0	9	1.0	10	ns
		Figure 1 C _L = 50pF	4.5V to 5.5V	-	5.2	10	1.0	11	1.0	12	115
t _{PD}	STCP to Qn	Figure 1 C _L = 15pF	4.5V to 5.5V	-	4	7.4	1.0	8.5	1.0	9.5	
Propagation Delay		Figure 1 C _L = 50pF	4.5V to 5.5V	-	5.3	9	1.0	10.5	1.0	11.5	ns
		Figure 1 C _L = 15pF	4.5V to 5.5V	_	4.6	8.2	1.0	9.5	1.0	10.5	
	MR to Q7S	Figure 1 C _L = 50pF	4.5V to 5.5V	_	5.8	10.5	1.0	11.5	1.0	12.5	ns
t _{EN}		Figure 1 C _L = 15pF	4.5V to 5.5V	-	4.8	9	1.0	11	1.0	12	
Enable Time	OE to Qn	Figure 1 C _L = 50pF	4.5V to 5.5V	_	6.2	11.6	1.0	13	1.0	14.5	ns
t _{DIS}		Figure 1 C _L = 15pF	4.5V to 5.5V	_	3.6	6.9	1.0	8	1.0	9	
Disable Time	OE to Qn	Figure 1 C _L = 50pF	4.5V to 5.5V	_	5.8	10.3	1.0	11	1.0	12	ns

Operating Characteristics (@T_A = +25°C, unless otherwise specified.)

Parameter		Test Conditions	V _{CC} = 5V Typ	Unit
C_{pd}	Power dissipation capacitance	f = 1 MHz all outputs switching-no load	42	pF

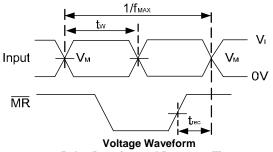


Parameter Measurement Information

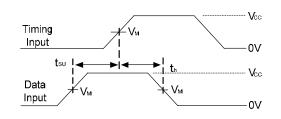


TEST	Vload		
tplh/tphl	Open		
t _{PLZ} /t _{PZL}	V _{CC}		
t _{PHZ} /t _{PZH}	GND		

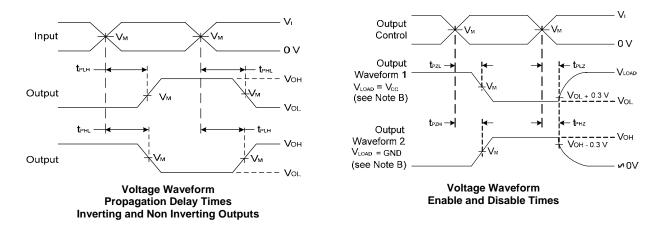
V	Inputs		v	м	C	
V _{cc}	VI	t _r /t _f	Input	Output	υL	
4.5V to 5.5V	3.0V	3ns	1.5V	V _{CC} /2	15pF, 50pF	



Pulse Duration and Recovery Time



Voltage Waveform Set-up and Hold Times



Notes:

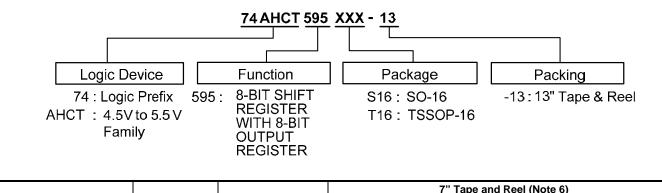
A. Includes test lead and test apparatus capacitance.

- B. Output Waveform 1 depends on the internal Q_N node being low and behaves in this manner based on OE pin.
 Output Waveform 2 depends on the internal Q_N node being high and behaves in this manner based on OE pin.
 C. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- D. Inputs are measured separately one transition per measurement.
- E. t_{PLH} and t_{PHL} are the same as t_{PD} .

Figure 1 Load Circuit and Voltage Waveforms



Ordering Information

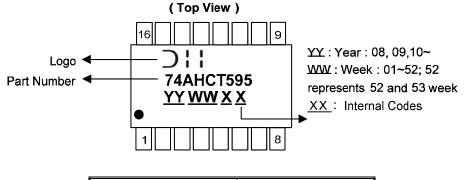


Part Number	Baakaga Cada	Bookoging	7" Tape and Reel (Note 6)			
Fait Nulliber	Package Code	Packaging	Quantity	Part Number Suffix		
74AHCT595S16-13	S16	SO-16	2500/Tape & Reel	-13		
74AHCT595T16-13	T16	TSSOP-16	2500/Tape & Reel	-13		

Note: 6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

Marking Information

(1) SO-16, TSSOP16



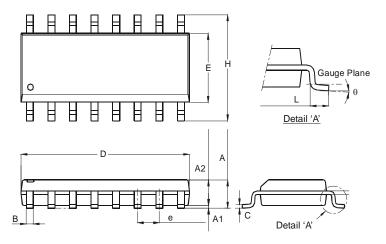
Part Number	Package		
74AHCT595S16	SO-16		
74AHCT595T16	TSSOP-16		



Package Outline Dimensions (All dimensions in mm.)

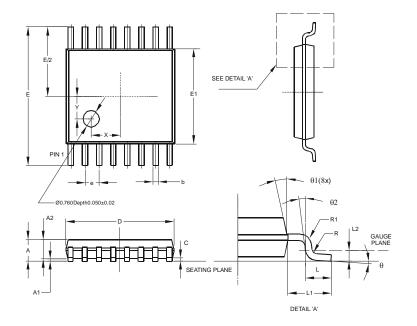
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

Package Type: SO-16



SO-16				
Dim	Min	Max		
Α	1.40	1.75		
A1	0.10	0.25		
A2	1.30	1.50		
В	0.33	0.51		
С	0.19	0.25		
D	9.80	10.00		
ш	3.80	4.00		
e	1.27 Typ			
Н	5.80	6.20		
L	0.38	1.27		
Θ	0°	8°		
All Dimensions in mm				

Package Type: TSSOP-16



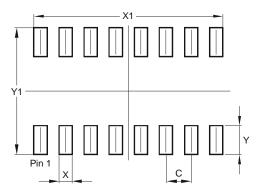
TSSOP-16				
Dim	Min	Max	Тур	
Α	-	1.08	-	
A1	0.05	0.15	-	
A2	0.80	0.93	-	
b	0.19	0.30	-	
С	0.09	0.20	-	
D	4.90	5.10	-	
Е	6.40 BSC			
E1	4.30	4.50	-	
e	0.65 BSC			
L	0.45	0.75	-	
L1	1.00 REF			
L2	0.25 BSC			
R	0.09	-	-	
R1	0.09	-	-	
X Y	-	-	1.350	
	-	-	1.050	
Θ	0°	8°	-	
Θ1	5°	15°	-	
Θ2	0°	-	-	
All Dimensions in mm				



Suggested Pad Layout

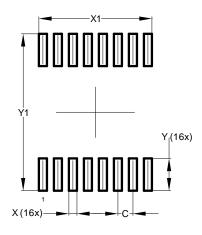
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

Package Type: SO-16



Dimensions	Value (in mm)	
С	1.270	
Х	0.670	
X1	9.560	
Y	1.450	
Y1	6.400	

Package Type: TSSOP-16



Dimensions	Value (in mm)	
С	0.650	
Х	0.350	
X1	4.900	
Y	1.400	
Y1	6.800	



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2013, Diodes Incorporated

www.diodes.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))